



Dual Bipolar/JFET, Precision Operational Amplifier

T-79-15

OP-285*

FEATURES

Low Offset Voltage: 250 μ V
 Wide Bandwidth: 8 MHz
 High Slew Rate: 20 V/ μ s
 Low Noise: 6 nV/ \sqrt Hz
 Low Distortion: 0.001%
 Low Supply Current: 5 mA
 Low Offset Current: 2 nA
 Unity-Gain Stable

APPLICATIONS

Active Filters
 Fast Amplifiers
 Integrators

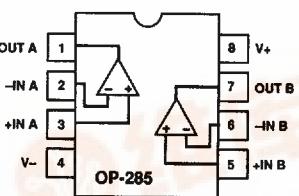
PIN CONNECTIONS

8-Lead Narrow-Body SOIC
 (S Suffix)



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8-Lead Epoxy DIP
 (P Suffix)



GENERAL DESCRIPTION

The OP-285 is a precision high speed amplifier featuring the Butler Amplifier front-end. This new front-end design combines the accuracy and low noise performance of bipolar transistors with the speed of JFETs. This yields an amplifier with high slew rates, low offset and good noise performance at low supply currents. Bias currents are also low compared to bipolar designs.

The OP-285 is specified over the extended industrial (-40°C to +85°C) temperature range. OP-285s are available in plastic DIP plus SO-8 surface mount packages.

*Patents pending.

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OP-285—SPECIFICATIONS

ELECTRICAL CHARACTERISTICS (@ $V_S = \pm 15.0$ V, $T_A = +25^\circ\text{C}$ unless otherwise specified.)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}			125	250	μV
Input Bias Current	I_B	$V_{CM} = 0$ V		150		nA
Input Offset Current	I_{OS}	$V_{CM} = 0$ V		2		nA
Input Voltage Range	V_{CM}		-10.5		+10.5	V
Common-Mode Rejection	CMR	$V_{CM} = \pm 10.5$ V	86			dB
Large Signal Voltage Gain	A_{VO}	$R_L = 600 \Omega$		200		V/mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$			5		$\mu\text{V}/^\circ\text{C}$
OUTPUT CHARACTERISTICS						
Output Voltage Swing	V_O	$R_L = 10 \text{ k}\Omega$	-13	± 14.1	+13	V
Open Loop Output Resistance	R_{OUT}					Ω
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_S = \pm 4.5$ V to ± 15 V		80		dB
Supply Current	I_{SY}	$V_O = 0$ V	4	5	± 18	mA
Supply Voltage Range	V_S					V
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 2 \text{ k}\Omega$		20		$\text{V}/\mu\text{s}$
Full-Power Bandwidth	BW_p					kHz
Settling Time	t_s					μs
Gain Bandwidth Product	GBP			8		MHz
Total Harmonic Distortion	THD	$\text{@ } 20 \text{ kHz}$	0.002			%
		$\text{@ } 1 \text{ kHz}$	0.0006			%
Phase Margin	θ_0			62		Degrees
NOISE PERFORMANCE						
Voltage Noise	$e_n \text{ p-p}$	0.1 Hz to 10 Hz		1.1		$\mu\text{V p-p}$
Voltage Noise Density	e_n	$f = 1 \text{ kHz}$		6		$\text{nV}/\sqrt{\text{Hz}}$
Current Noise Density	i_n	$f = 1 \text{ kHz}$		1.5		$\text{pA}/\sqrt{\text{Hz}}$

Specifications subject to change without notice.

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OP-285

WAFER TEST LIMITS @ $V_s = \pm 15.0$ V, $T_A = +25^\circ\text{C}$ unless otherwise specified.)

Parameter	Symbol	Conditions	Limit	Units
Offset Voltage	V_{OS}		250	mV max
Input Bias Current	I_B	$V_{CM} = 0$ V	200	nA max
Input Offset Current	I_{OS}	$V_{CM} = 0$ V	50	nA max
Input Voltage Range ¹			± 10.5	V min
Common-Mode Rejection	CMRR	$V_{CM} = \pm 10.5$ V	86	dB min
Power Supply Rejection Ratio	PSRR	$V = \pm 4.5$ V to ± 15 V	80	dB min
Large Signal Voltage Gain	A_{VO}	$R_L = 10$ k Ω	100	V/mV min
Output Voltage Range	V_O	$R_L = 10$ k Ω	± 13	V min
Supply Current	I_{SY}	$V_O = 0$ V, $R_L = \infty$	5	mA max

NOTE

Electrical tests and wafer probe to the limits shown. Due to variations in assembly methods and normal yield loss, yield after packaging is not guaranteed for standard product dice. Consult factory to negotiate specifications based on die lot combinations through sample lot assembly and testing.

¹Guaranteed by CMR test.

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PRELIMINARY
TECHNICAL
DATA

ORDERING GUIDE

ABSOLUTE MAXIMUM RATINGS ¹	
Supply Voltage	± 18 V
Input Voltage ²	± 18 V
Differential Input Voltage ²	± 7.5 V
Output Short-Circuit Duration	Limited
Storage Temperature Range	
P, S Package	-65°C to $+150^\circ\text{C}$
Operating Temperature Range	
OP-285E, F	-40°C to $+85^\circ\text{C}$
Junction Temperature Range	
P, S Package	-65°C to $+150^\circ\text{C}$
Lead Temperature Range (Soldering, 60 Sec)	$+300^\circ\text{C}$

Model	Temperature Range	Package Option*
OP285EP	-40°C to $+85^\circ\text{C}$	8-Pin Plastic DIP
OP285ES	-40°C to $+85^\circ\text{C}$	8-Pin SOIC
OP285FP	-40°C to $+85^\circ\text{C}$	8-Pin Plastic DIP
OP285FS	-40°C to $+85^\circ\text{C}$	8-Pin SOIC
OP285GBC	$+25^\circ\text{C}$	DICE

*For outline information see Package Information section.

Package Type	θ_{JA} ³	θ_{JC}	Units
8-Pin Plastic DIP (P)	103	43	°C/W
8-Pin SOIC (S)	158	43	°C/W

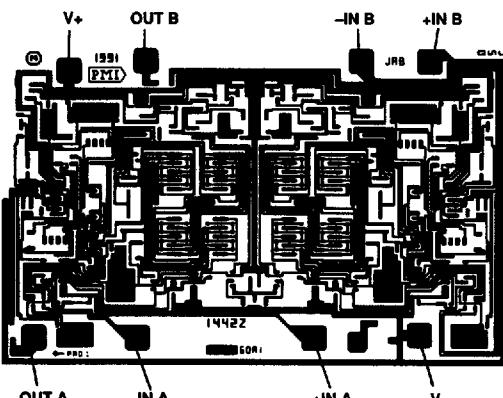
NOTES

¹Absolute maximum ratings apply to both DICE and packaged parts, unless otherwise noted.

²For supply voltages less than ± 18 V, the absolute maximum input voltage is equal to the supply voltage.

³ θ_{JA} is specified for the worst case conditions, i.e., θ_{JA} is specified for device in socket for cerdip, P-DIP, and LCC packages; θ_{JA} is specified for device soldered in circuit board for SOIC package.

DICE CHARACTERISTICS



OP-285 Die Size 0.070 in. \times 0.106 in. (7,560 sq. mils)